## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Ting, et al.

Attorney Docket:

TSM03-0945

Filed:

Herewith

Examiner:

TBD

Serial No.:

**TBD** 

Art Unit:

TBD

For:

Notched Spacer for CMOS Transistors

Mail Stop: Patent Application Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

## INFORMATION DISCLOSURE STATEMENT

The Applicant wishes to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08A that may be considered material to the examination of the above-identified application.

No fee is due at this time, as this Information Disclosure Statement is being filed concurrently with the patent application.

Pursuant to 37 CFR 1.98(a)(2)(i), as amended, copies of U.S. Patents cited are not being submitted. However, Applicant has included copies of any non-patent literature.

Respectfully submitted,

Date

May 6, 2004

Attorney for Applicant

Reg. No. 46,836

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PTO/SB/08a (08-03)
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Substitute for form 1449A/PTO				Complete if Known		
				Application Number	TBD	
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STATEMENT BY APPLICANT			ANT	First Named Inventor	Ting, et al.	
	(Use as many sheets as necessary)			Art Unit	TBD	
				Examiner Name	TBD	
Sheet	1	of	1	Attorney Docket Number	TSM03-0945	

U.S. PATENT DOCUMENTS						
	T	Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where	
Examiner Initials*	Cite No.1	Number - Kind Code <sup>2 (if known)</sup>	MM-DD-YYYY	Applicant of Cited Document	Relevant Passages or Relevant Figures Appear	
		US-2003/0067045 A1	04-10-2003	Sugiyama et al.		
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No.1	Foreign Patent Document  Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> ( <i>if known</i> )	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
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NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>	
		GHANI, T. et al., "100 nm Gate Length High Performance/Low Power CMOS Transistor Structure," IEDM (1999) pp. 415-418.		
		NAKAI, S., et al., "A 100 nm CMOS Technology with "Sidewall-Notched" 40 nm Transistors and SiC-Capped Cu/VLK Interconnects for High Performance Microprocessor Applications," 2002 Symposium on VLSI Technology Digest of Technical Papers (2002) pp. 66-67.		
		PIDIN, S., et al., "Experimental and Simulation Study on Sub-50 nm CMOS Design," 2001 Symposium on VLSI Technology Digest of Technical Papers (2001) pp. 35-36.		

Examiner	Date	
Signature	Considered	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 'Applicant's unique citation designation number (optional). 'See Kinds Codes of USPTO Patent Documents at <a href="www.uspto.gov">www.uspto.gov</a> or MPEP 901.04. 'Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 'For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 'Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. 'Applicant is to place a check mark here if English language Translation is attached.' Translation is attached.

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